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This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Amended) An integrated circuit switch comprising:

at least two signal ports coupled by a signal path, the signal path including a channel of at least one series FET;

a shunt path coupled to ground and including a channel of a shunt FET;

a first control voltage applied to the signal path; and,

a second control voltage applied to a gate of the series FET and to a drain/source of the shunt FET,

wherein the shunt path includes at least one feedforward capacitor.

2. (Previously Amended) A method for switching a signal so as to selectively connect a first port in an integrated circuit to a second port in the integrated circuit, comprising:

providing a series switch in a signal path between the first port and the second port; providing a shunt switch in a shunt path coupled to ground; providing at least one feedforward capacitor in the shunt path; providing a first control voltage applied to the signal path; and, using a common logic signal to control both the series switch and the shunt switch.

Claims 3-5 (Canceled).

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6. (Currently Amended) A switch for coupling a first port to a second port, comprising:

a first control signal input;

a second control signal input coupled between the first port and the second port;

a FET connected in series between the first port and the second port, said series FET

having a gate coupled to the first control signal input; and

means for enhancing the isolation between the first and second ports, and for improving

the harmonic noise rejection of the switch, the isolation and harmonic rejection means having an

input coupled to the first control signal input and to the gate of the series FET, whereby a single

control signal is applied to both the series FET and the isolation and harmonic rejection means,

via the first control signal input, in order to turn the series FET on and simultaneously turn the

isolation means off and, conversely, in order to turn the series FET off and simultaneously turn

the isolation means on.

7. (Original) The switch of claim 6, wherein the isolation and harmonic rejection means includes

a shunt path including a shunt FET, the shunt FET having a drain coupled to the control signal

input and to the gate of the series FET, whereby the single control signal is applied to both the

series FET and the shunt FET, via the control signal input, in order to turn the series FET on and

simultaneously turn the shunt FET off and, conversely, in order to turn the series FET off and

simultaneously turn the shunt FET on, the harmonic rejection is provided without the need of a

separate feedforward capacitor.

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8. (Previously Amended) A method of controlling the coupling of a first port to a second port via

a series/shunt FET switch, comprising the steps of:

providing a first control voltage between the first port and the second port;

providing at least one feedforward capacitor coupled to a shunt FET;

isolating the first port from the second port, using a single control signal, by turning off a

series FET by biasing the gate-source voltage of the series FET below the pinchoff voltage, and

by turning the shunt FET on by biasing the gate-source voltage above the pinchoff voltage; and

coupling the first port to the second port, using a single control signal, by turning on the

series FET by biasing the gate-source voltage above the pinchoff voltage, and turning the shunt

FET off by biasing the gate-source voltage above the pinchoff voltage.

9. (Previously Amended) An integrated circuit for selectively connecting and disconnecting a

first RF port to or from a second RF port, comprising:

a signal path connecting the first RF port and the second RF port;

a first control electrode coupled to the signal path;

at least one series switching transistor having a signal path and a second control electrode,

a first control voltage applied to the second control electrode permitting a signal to pass, a second

control voltage applied to the second control electrode rendering the current path to be of high

impedance; and

a shunt transistor having a diverging signal path, one end of the signal path of the shunt

transistor coupled to the second control electrode of said at least one series switching transistor, a

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second end of the signal path of the shunt transistor coupled through a low signal impedance to

the signal ground reference; additionally allowing for control of the shunt transistor signal path

impedance by application of the first control voltage to both the second control electrode of the

series switching transistor and simultaneously to the drain and/or source of the shunt transistor

rendering the signal path of the shunt transistor substantially nonconductive while the series

switching transistor signal path is conductive, and wherein application of the second control

voltage to the shunt transistor renders the signal path of the shunt transistor conductive while the

series switching transistor path is simultaneously nonconductive with the same second control

voltage simultaneously applied to its second control electrode to thereby increase the isolation

between the first and second RF ports,

wherein said shunt transistor is coupled to at least one feedforward capacitor.

10. (Previously Amended) The integrated circuit of Claim 9, wherein said at least one switching

transistor is a field effect transistor.

11. (Original) The integrated circuit of Claim 9, wherein said at least one switching transistor is

an insulated gate field effect transistor.

12. (Canceled).

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13. (Original) The integrated circuit of Claim 9, wherein the shunt transistor is a field effect

transistor.

14. (Original) The integrated circuit of Claim 13, wherein the shunt transistor is an insulated gate

field effect transistor.

15. (Previously Amended) The integrated circuit of Claim 14, wherein a drain of the shunt

transistor is coupled to the second control electrode of said at least one switching transistor, the

first and second control voltages being applied to the drain.

16. (Canceled).

17. (Canceled).

18. (Original) The integrated circuit of Claim 9, wherein the signal path of the shunt transistor is

coupled to the signal ground reference through a shunt capacitor.

19. (Previously Amended) The integrated circuit of Claim 9, wherein the first control voltage

provides a voltage differential across the series switching transistor.

Claims 20-23 (Canceled).

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